

★Under Development

8 Diode

Switching

Type No	Maximum Ratings				Electrical Characteristics (Ta = 25°C) MAX						Package	Fig
	V _{RM}	I _{FM}	I _O	P	V _F	I _F	I _R	C _T	t _{rr}	Condition		
	(V)	(mA)	(mA)	(mW)	(V)	(mA)	(μA)	f:1MHz (pF)	(ns)	(V)		
KDS1553	70				1.4	100	0.5	3.5			DO-35	F37
KDS1554	55	300	100	300								
KDS1555	35											
IN4148	75	225	100	500	1.0	10	0.025	4.0				
KDS176	35	300	100	300	1.2	100	0.5	3.0				
KDS181S											1-2HIA	F38
KDS184S										V _R = 6V R _L = 100Ω	KDS 181S	KDS 184S
KDS187S										I _F = 10mA	KDS 187S	KDS 190S
KDS190S									4		KDS 187S	KDS 190S
KDS193S											KDS 193S	KDS 196S
KDS196S											KDS 193S	KDS 196S
★KDS226S	80	300	100	150	1.2	100	0.5	3.0			KDS 226S	KDS 200
KDS200											KDS 200	KDS 227
KDS201				200				4.0			KDS 201	KDS 227
★KDS227											KDS 201	KDS 227

Temperature Bias Compensation

Type No	V _R	I _{FM}	I _{FAV}	T _J	V _F			I _R		V _F		Package	Fig
					MIN	TYP	MAX	I _F	MAX	TYP	I _F		
KS8513A-0	5	150	50	150	0.63	0.65	0.68	3	10	-2.0	1	DO-35	F37

AFC diode

*Under Development

Type No	V_R (V)	T_J (°C)	MAX			Cr			K		Q 1~50MHZ		Package	Fig
			I_R (nA)	V_R (V)	MIN (PF)	MAX (PF)	VR (V)	f (MHZ)	MIN	MAX	TYP	V_T (V)		
*KDV147	15	125	50	15	11.7	13.7	8	1	—	—	—	—	TO-92M(C)	F5
*KDV149	15	125	50	15	—	30	8	1	—	—	450	1	TO-92M	F39
KDS2236	15	150	100	4	7	14	4	1	0.21	0.5	120	4	DO-35	F37

Schottky Barrier Diode

Type No	V_{RRM} (V)	I_{FRM} (A)	I_{FSM} (A)	$I_F(AV)$ (A)	T_J (°C)	$V_F(Max)$ (V) $I_O=15A$	I_R (mA) ($T_C=25^{\circ}C$)	$R_{th}(J-C)$ °C/W	$R_{th}(J-A)$ °C/W	Package	Fig
KDB1545	45	15	150	7.5	-65~+150	0.70	0.1	3.0	60	TO-220AB(b)	F6

Rectifier

Type No	V_{RM} (V)	V_{RSM} (V)	I_O (A)	I_{SURGE}	T_J (°C)	T_{sig} (°C)	V_F (V)	MAX I_F (A)	I_R (μA)	MAX V_{RM} (V)	Package	Fig
IN4001	50	100	1	50	175	-65~175	1.1	1	10	RATED	DO-41	F36
IN4002	100	200		50								
IN4003	200	300		50								
IN4004	400	500		50								
IN4005	600	750		30								
IN4006	800	1000		30								
IN4007	1000	1200		30								